FAIRCHILD SEMICONDUCTOR™

December 2000

QFET™

FQD4N20L / FQU4N20L

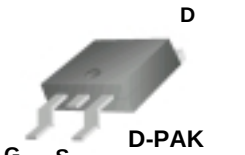
200V LOGIC N-Channel MOSFET

General Description

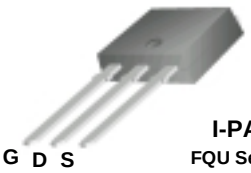
These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.
This advanced technology is especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation modes. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, and motor control.

Features

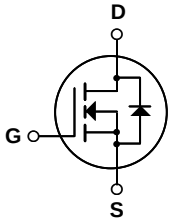
- 3.2A, 200V, $R_{DS(on)}$ = 1.35Ω @V_{GS} = 10 V
- Low gate charge (typical 4.0 nC)
- Low Crss (typical 6.0 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- Low level gate drive requirement allowing direct operation from logic drivers



D-PAK
FQD Series



I-PAK
FQU Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQD4N20L / FQU4N20L	Units
V_{DSS}	Drain-Source Voltage		200	V
I_D	Drain Current - Continuous (T_C = 25°C)		3.2	A
	- Continuous (T_C = 100°C)		2.02	A
I_{DM}	Drain Current - Pulsed	(Note 1)	12.8	A
V_{GSS}	Gate-Source Voltage		± 20	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	52	mJ
I_{AR}	Avalanche Current	(Note 1)	3.2	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	3.0	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P_D	Power Dissipation (T_A = 25°C) *		2.5	W
	Power Dissipation (T_C = 25°C)		30	W
	- Derate above 25°C		0.24	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	4.17	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient *	--	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	°C/W

* When mounted on the minimum pad size recommended (PCB Mount)

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Electrical Characteristics

T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	200	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.16	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 200 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 160 V, T_C = 125°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 20 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -20 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	1.0	--	2.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 1.6 A V_{GS} = 5 V, I_D = 1.6 A	--	1.10 1.13	1.35 1.40	Ω
g_{FS}	Forward Transconductance	V_{DS} = 25 V, I_D = 1.6 A (Note 4)	--	3.0	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	240	310	pF
C_{oss}	Output Capacitance		--	36	45	pF
C_{rss}	Reverse Transfer Capacitance		--	6	8	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 100 V, I_D = 3.8 A, R_G = 25 Ω (Note 4, 5)	--	7	25	ns
t_r	Turn-On Rise Time		--	70	150	ns
$t_{d(off)}$	Turn-Off Delay Time		--	15	40	ns
t_f	Turn-Off Fall Time		--	40	90	ns
Q_g	Total Gate Charge	V_{DS} = 160 V, I_D = 3.8 A, V_{GS} = 5 V (Note 4, 5)	--	4.0	5.2	nC
Q_{gs}	Gate-Source Charge		--	1.0	--	nC
Q_{gd}	Gate-Drain Charge		--	1.9	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	3.2	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	12.8	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 3.2 A	--	--	1.5	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 3.8 A, dI_F / dt = 100 A/μs (Note 4)	--	90	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.25	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 7.6mH, I_{AS} = 3.2A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 3.8A, di/dt ≤ 300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

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Typical Characteristics

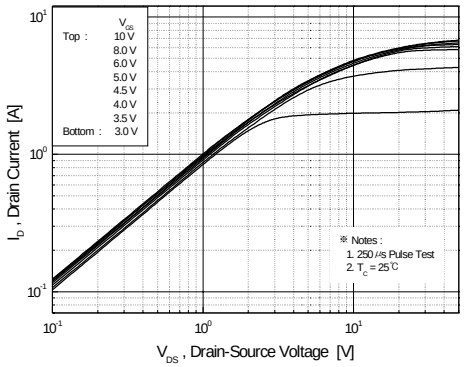


Figure 1. On-Region Characteristics

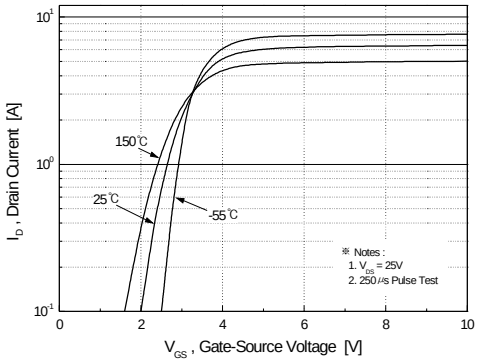


Figure 2. Transfer Characteristics

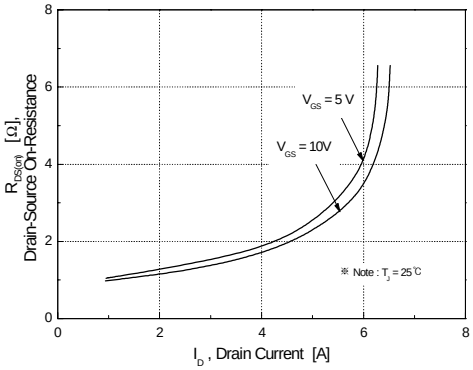


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

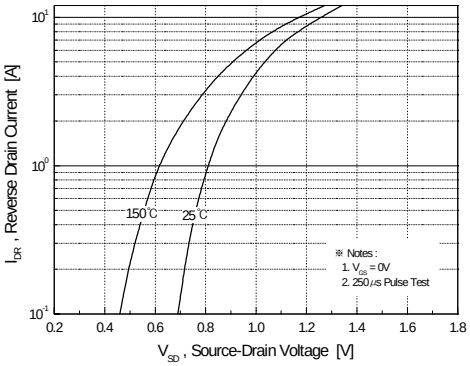


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

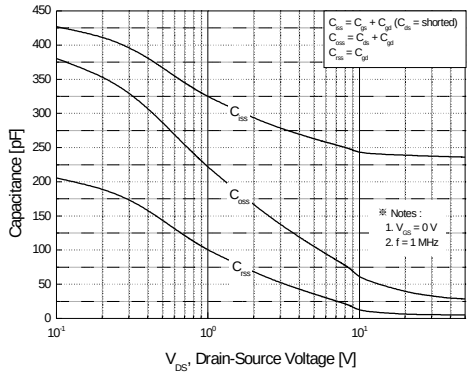


Figure 5. Capacitance Characteristics

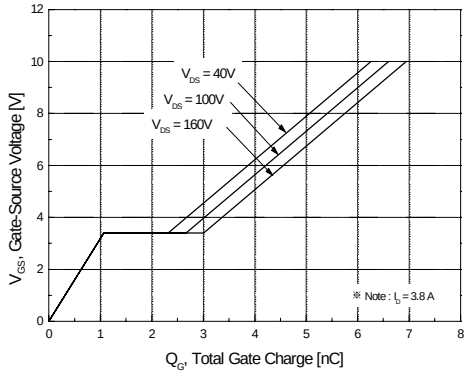


Figure 6. Gate Charge Characteristics

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Typical Characteristics (Continued)

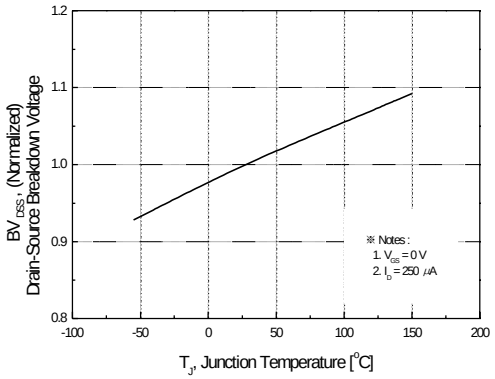


Figure 7. Breakdown Voltage Variation vs. Temperature

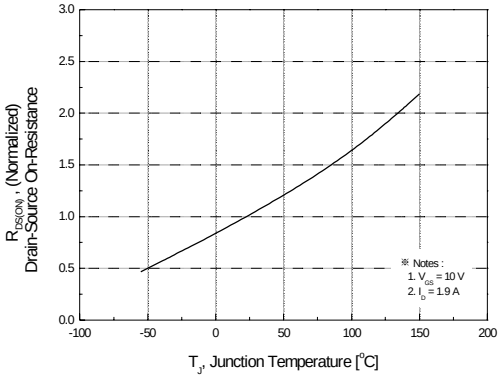


Figure 8. On-Resistance Variation vs. Temperature

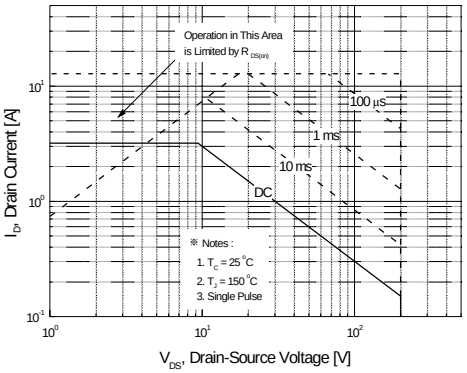


Figure 9. Maximum Safe Operating Area

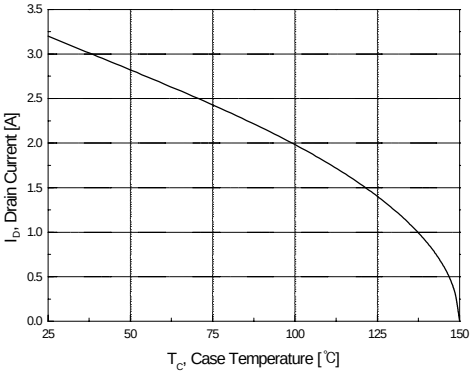


Figure 10. Maximum Drain Current vs. Case Temperature

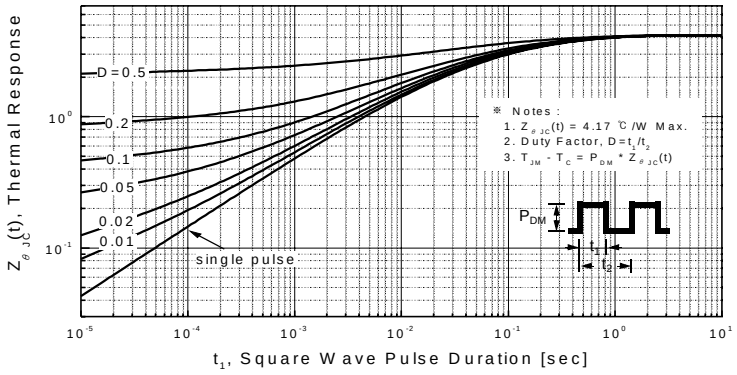
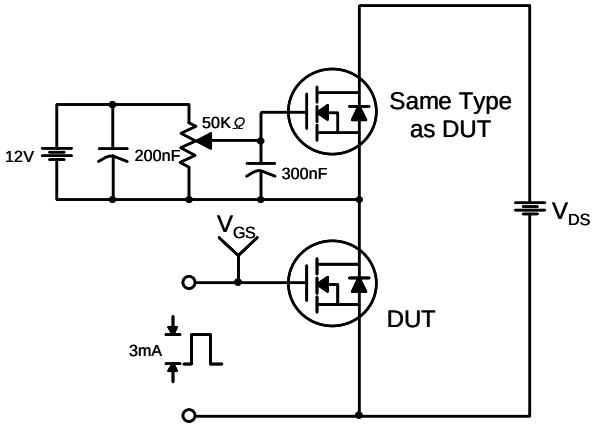
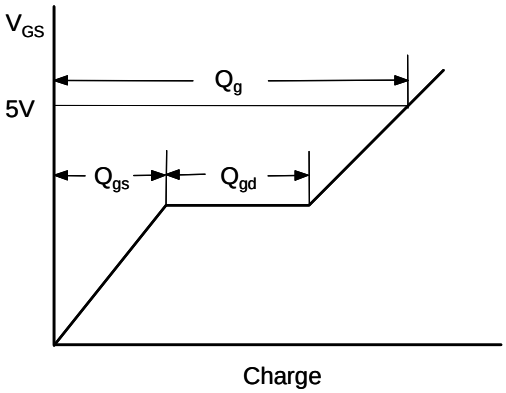


Figure 11. Transient Thermal Response Curve

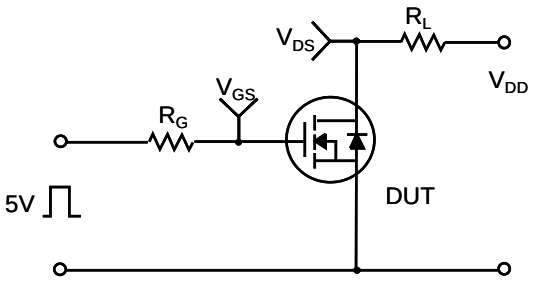
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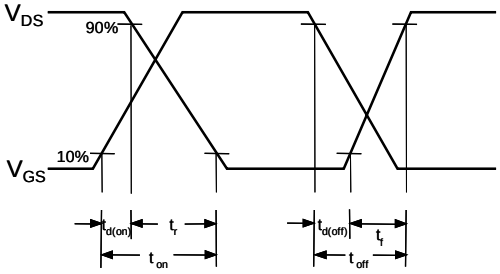
Gate Charge Test Circuit & Waveform



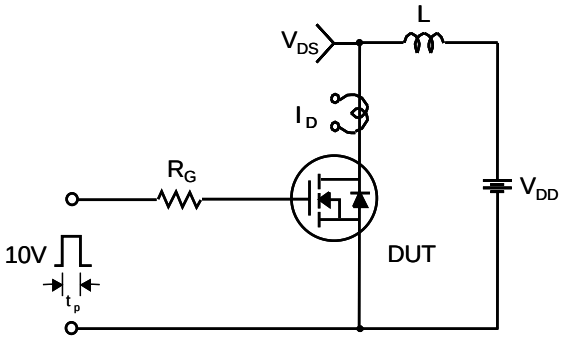


Resistive Switching Test Circuit & Waveforms

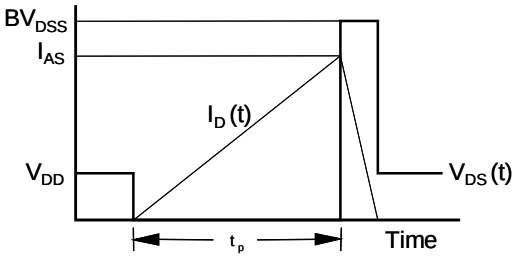




Unclamped Inductive Switching Test Circuit & Waveforms

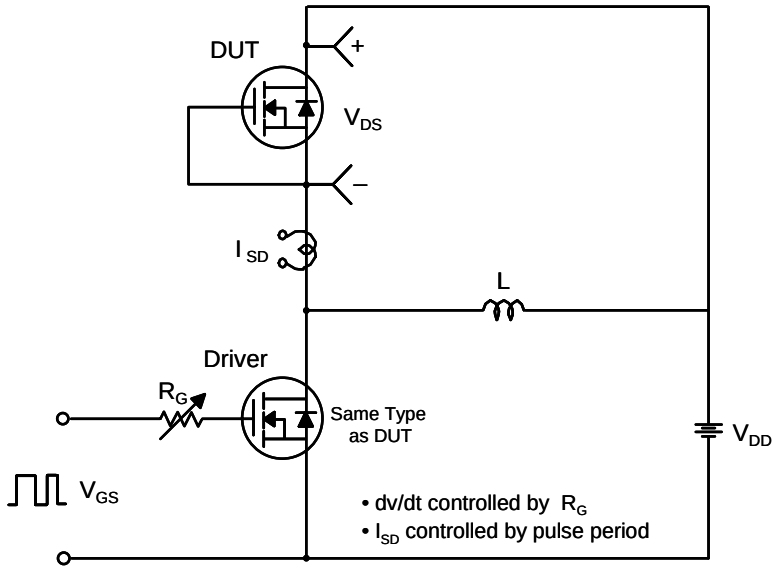


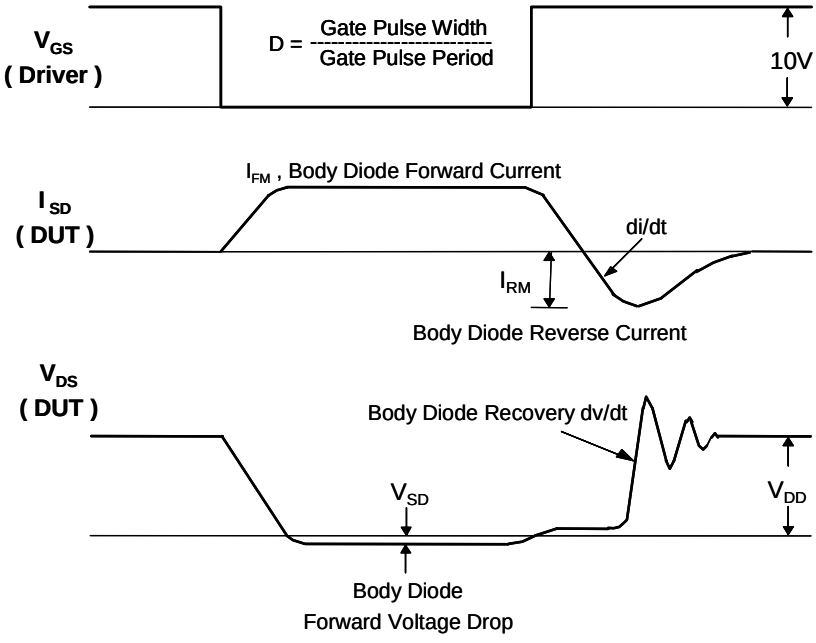
$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



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Peak Diode Recovery dv/dt Test Circuit & Waveforms

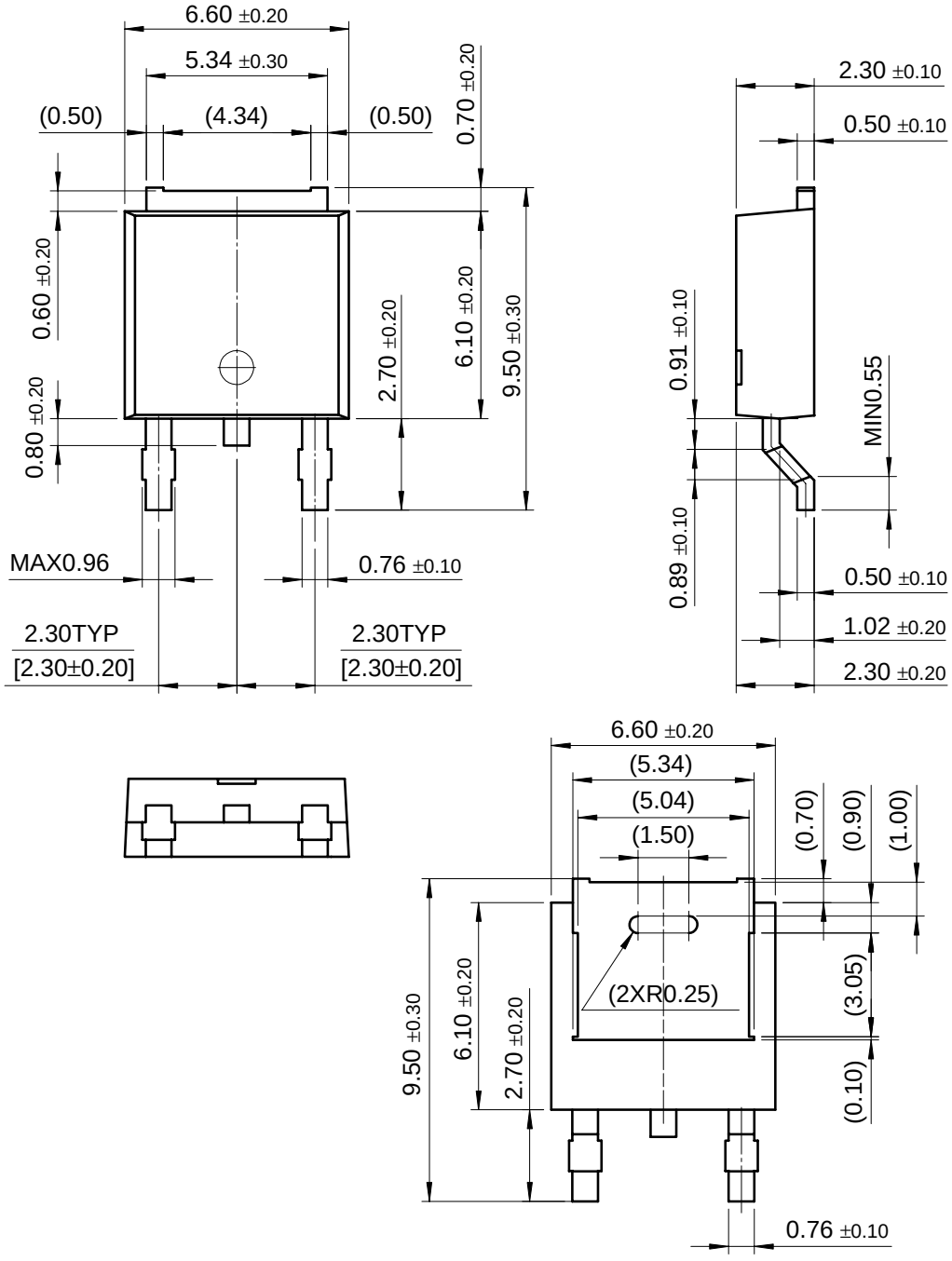




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Package Dimensions

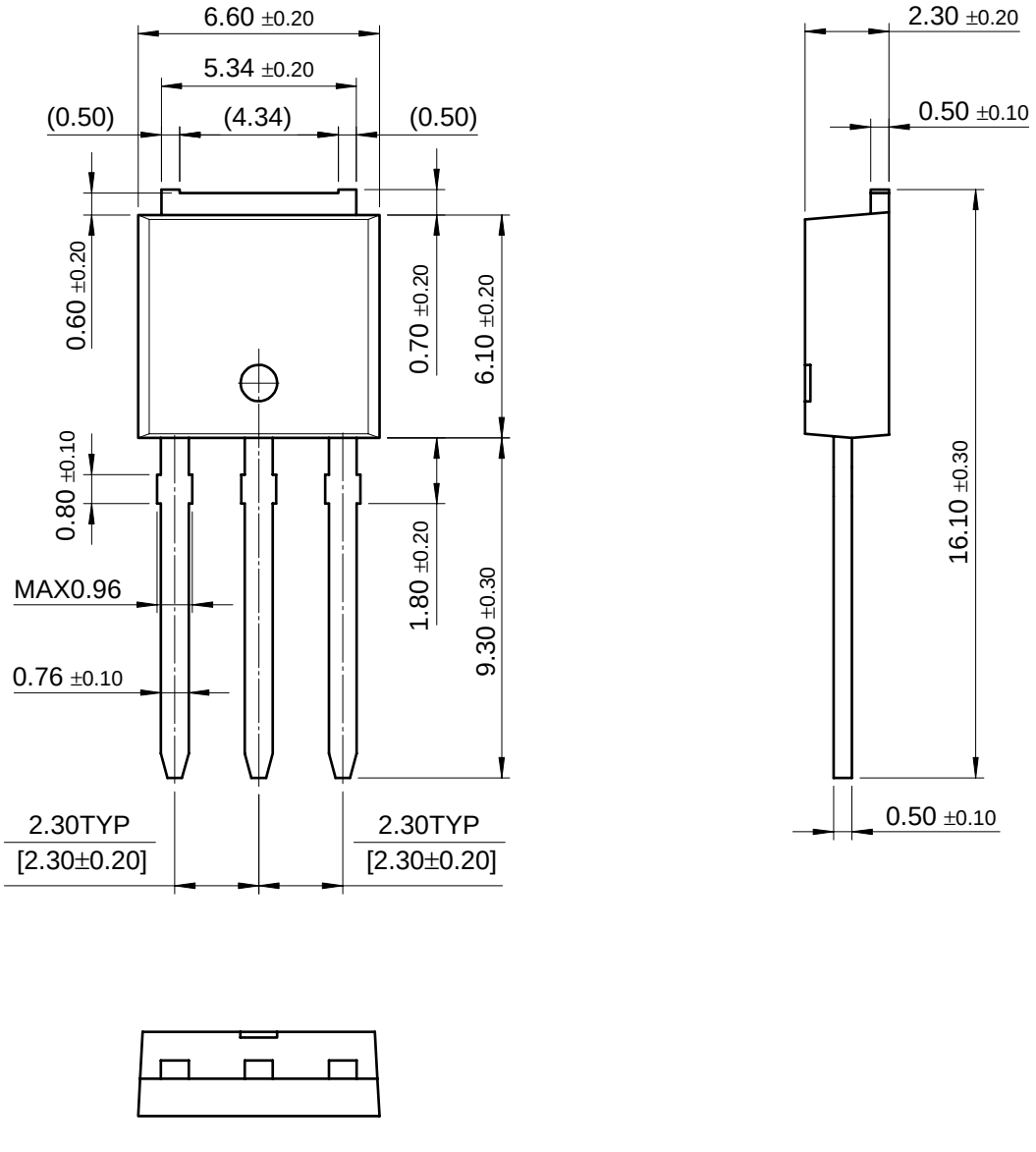
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Package Dimensions (Continued)

IPAK



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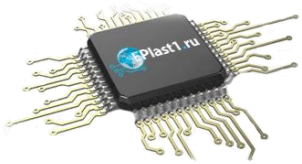
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- Подбор аналогов;
- Консультации по применению компонента;
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- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



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